

N-channel TrenchMOS standard level FET

Rev. 03 — 26 January 2011

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V and 24 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1.	Quick reference	data				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	55	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 3</u> ; see <u>Figure 1</u>	-	-	11	A
P _{tot}	total power dissipation	$T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 2}}{\text{Figure 2}}$	-	-	36	W
Static cha	aracteristics					
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I _D = 5 A; T _j = 25 °C; see <u>Figure 10</u> ; see Figure 11	-	127	150	mΩ



N-channel TrenchMOS standard level FET

Table 1.	Quick reference da	tacontinued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanch	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 11 \text{ A}; \text{V}_{\text{sup}} \leq 55 \text{ V}; \\ R_{\text{GS}} &= 50 \Omega; \text{V}_{\text{GS}} = 10 \text{V}; \\ T_{j(\text{init})} &= 25 ^{\circ}\text{C}; \text{ unclamped} \end{split} $	-	-	16	mJ
Dynamic	characteristics					
Q _{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 3 A; V _{DS} = 44 V; T _j = 25 °C; see <u>Figure 12</u>	-	2.7	-	nC

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	drain ^[1]	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT428 (DPAK)	

[1] It is not possible to make a connection to pin 2.

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BUK72150-55A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

N-channel TrenchMOS standard level FET

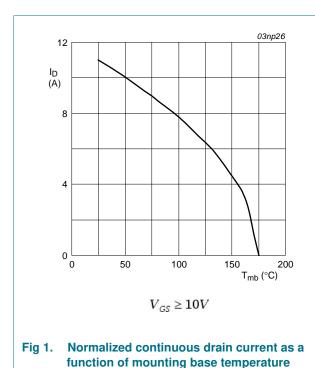
4. Limiting values

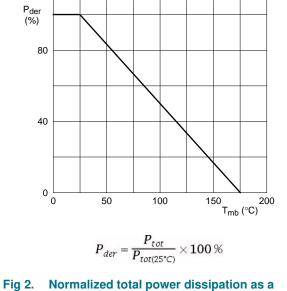
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	55	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	55	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; see <u>Figure 3</u> ; see <u>Figure 1</u>	-	11	А
		T_{mb} = 100 °C; V_{GS} = 10 V; see <u>Figure 1</u>	-	7	А
I _{DM}	peak drain current	T _{mb} = 25 °C; pulsed; t _p ≤ 10 μs; see <u>Figure 3</u>	-	44	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	36	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drain	diode				
I _S	source current	T _{mb} = 25 °C	-	11	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	44	А
Avalanche ru	ggedness				
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{array}{l} I_{D} = 11 \; A; \; V_{sup} \leq 55 \; V; \; R_{GS} = 50 \; \Omega; \\ V_{GS} = 10 \; V; \; T_{j(init)} = 25 \; ^{\circ}C; \; unclamped \end{array}$	-	16	mJ

120



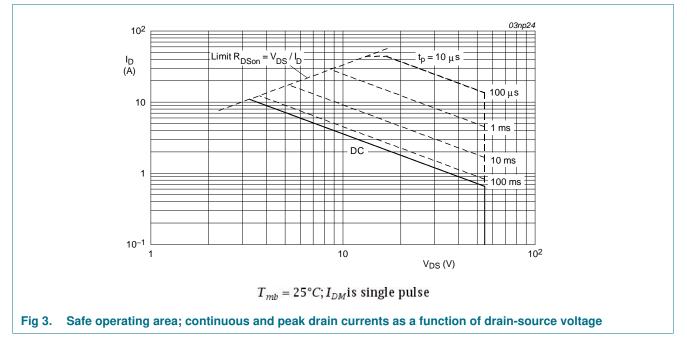


function of mounting base temperature

03na19

BUK72150-55A

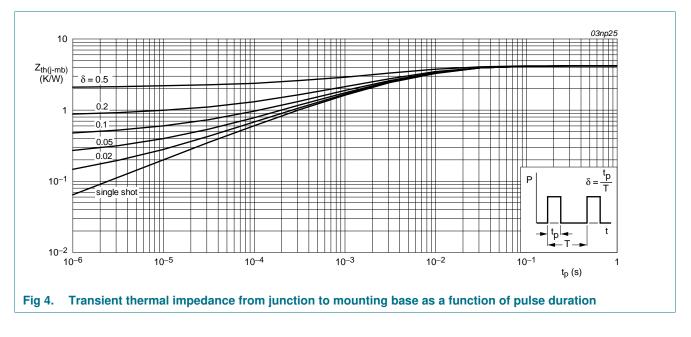
N-channel TrenchMOS standard level FET



5. Thermal characteristics

Table 5.Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th}(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 4</u>	-	-	4.1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient		-	71	-	K/W



All information provided in this document is subject to legal disclaimers.

BUK72150-55A

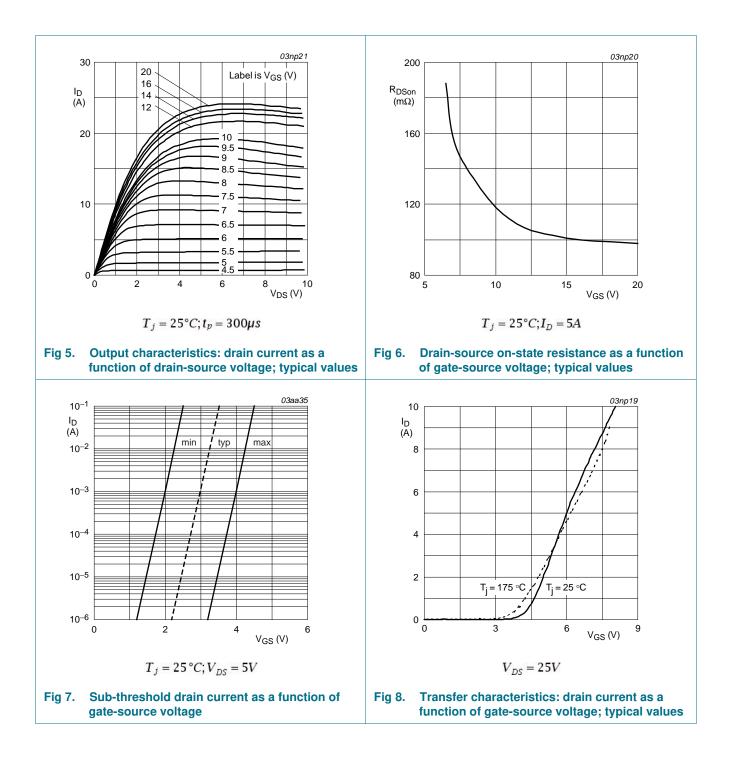
N-channel TrenchMOS standard level FET

6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source	$I_D = 0.25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	55	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 9</u>	2	3	4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 9</u>	1	-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 9</u>	-	-	4.4	V
I _{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μA
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; \text{ V}_{DS} = 0 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	2	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R_{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 5 A; T _j = 175 °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	-	-	300	mΩ
		V_{GS} = 10 V; I _D = 5 A; T _j = 25 °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	-	127	150	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 3 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$	-	5.5	-	nC
Q _{GS}	gate-source charge	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{12}$	-	1	-	nC
Q _{GD}	gate-drain charge		-	2.7	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	242	322	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } Figure 13$	-	40	48	pF
C _{rss}	reverse transfer capacitance		-	25	35	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 25 \text{ V}; \text{ R}_{L} = 2.7 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	3	-	ns
t _r	rise time	$R_{G(ext)} = 5.6 \ \Omega; \ T_{j} = 25 \ ^{\circ}C$	-	26	-	ns
t _{d(off)}	turn-off delay time		-	8	-	ns
t _f	fall time		-	10	-	ns
L _D	internal drain inductance	measured from drain to center of die ; $T_j = 25 \text{ °C}$	-	2.5	-	nH
L _S	internal source inductance	measured from source lead to source bond pad ; $T_j = 25 \text{ °C}$	-	7.5	-	nH
Source-d	rain diode					
V _{SD}	source-drain voltage	$I_S = 10 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see Figure 14	-	1.25	1.5	V
t _{rr}	reverse recovery time	$I_{S} = 10 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s};$	-	32	-	ns
Q _r	recovered charge	V_{GS} = -10 V; V_{DS} = 30 V; T_j = 25 °C	-	50	-	nC

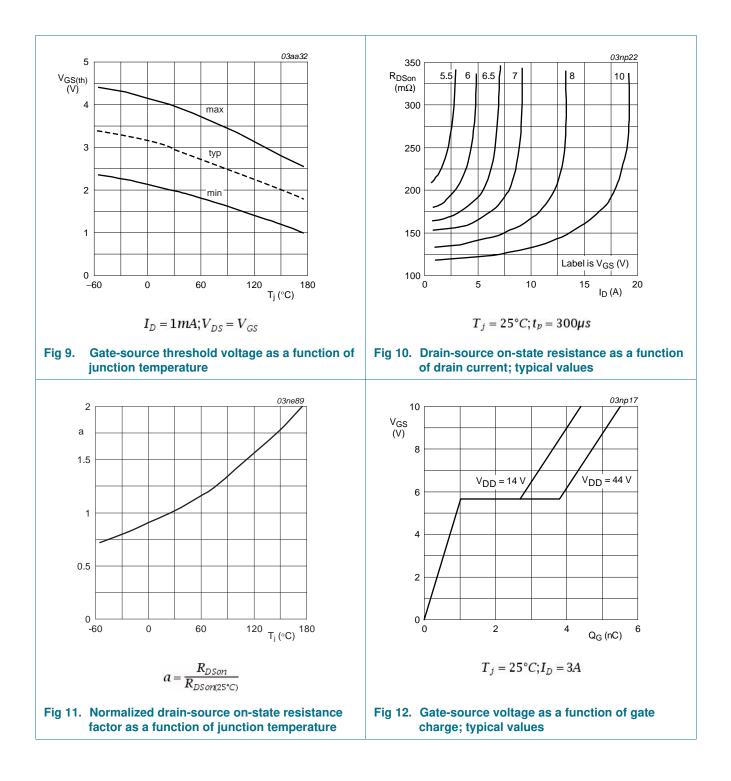
BUK72150-55A

N-channel TrenchMOS standard level FET



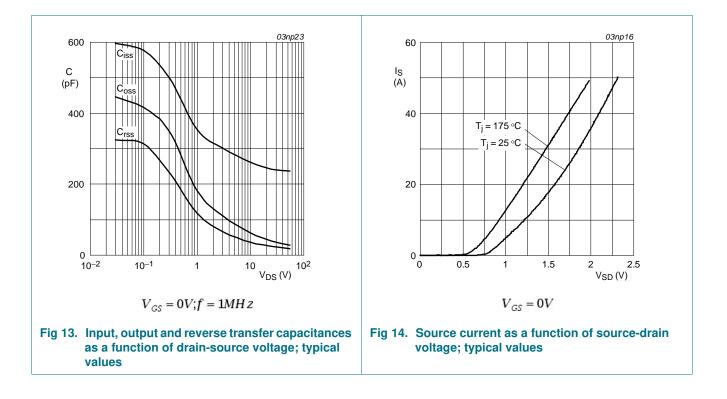
BUK72150-55A

N-channel TrenchMOS standard level FET



BUK72150-55A

N-channel TrenchMOS standard level FET



N-channel TrenchMOS standard level FET

7. Package outline

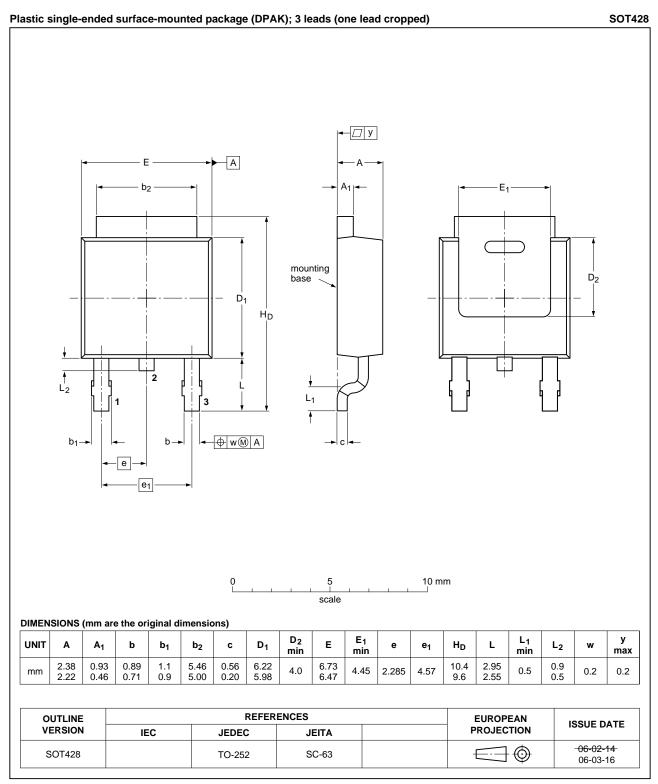


Fig 15. Package outline SOT428 (DPAK)

BUK72150-55A Product data sheet

© Nexperia B.V. 2017. All rights reserved

9 of 13

N-channel TrenchMOS standard level FET

8. Revision history

Table 7. Revision I	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK72150-55A v.3	20110126	Product data sheet	-	BUK72150-55A v.2
Modifications:	 The format of t of NXP Semice 		lesigned to comply with	n the new identity guidelines
	 Legal texts have 	ve been adapted to the new	company name where	appropriate.
	 Various chang 	es to content.		
BUK72150-55A v.2 (9397 750 12335)	20031120	Product data sheet	-	-

N-channel TrenchMOS standard level FET

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <u>http://www.nexperia.com</u>.

9.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Nexperia does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Nexperia sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between Nexperia and its customer, unless Nexperia and

customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the Nexperia product is deemed to offer functions and qualities beyond those described in the Product data sheet.

9.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, Nexperia does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

In no event shall Nexperia be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, Nexperia's aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of Nexperia.

Right to make changes — Nexperia reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use in automotive applications — This Nexperia product has been qualified for use in automotive

applications. The product is not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of a Nexperia product can reasonably be expected to result in personal injury, death or severe property or environmental damage. Nexperia accepts no liability for inclusion and/or use of Nexperia products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. Nexperia makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using Nexperia products, and Nexperia accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the Nexperia product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

Nexperia does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using Nexperia products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). Nexperia does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale - Nexperia

products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nexperia.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual

N-channel TrenchMOS standard level FET

agreement is concluded only the terms and conditions of the respective agreement shall apply. Nexperia hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of Nexperia products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

10. Contact information

For more information, please visit: http://www.nexperia.com

For sales office addresses, please send an email to: salesaddresses@nexperia.com

9.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

N-channel TrenchMOS standard level FET

11. Contents

1	Product profile1
1.1	General description1
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values3
5	Thermal characteristics4
6	Characteristics5
7	Package outline9
8	Revision history10
9	Legal information11
9.1	Data sheet status11
9.2	Definitions11
9.3	Disclaimers
9.4	Trademarks12
10	Contact information12